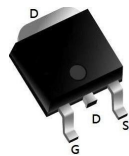
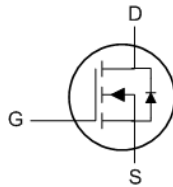


Description

The 60N02 is the high cell density trench N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The 60N02 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

100% EAS Guaranteed
Green Device Available
Super Low Gate Charge
Excellent CdV/dt effect decline
Advanced high cell density Trench technology

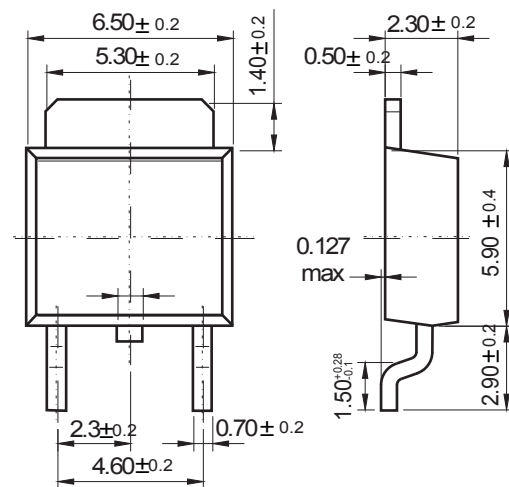


Product Summary

BVDSS	RDSON	ID
20 V	4.5mΩ	60 A

TO-252

Unit: mm



Dimensions in inches and (millimeters)

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	60	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	35	A
I_{DM}	Pulsed Drain Current ²	240	A
EAS	Single Pulse Avalanche Energy ³	48	mJ
I_{AS}	Avalanche Current	31	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	38	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4.2	$^\circ C/W$

60N02

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.4	0.7	1.0	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =4.5V, I _D =25A	-	4.5	6.5	mΩ
		V _{GS} =2.5V, I _D =15A	-	6.8	10	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1.0MHz	-	1832	-	pF
C _{oss}	Output Capacitance		-	289	-	pF
C _{rss}	Reverse Transfer Capacitance		-	271	-	pF
Q _g	Total Gate Charge	V _{DS} =10V, I _D =25A, V _{GS} =4.5V	-	23	-	nC
Q _{gs}	Gate-Source Charge		-	4.5	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	7.3	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =10V, I _D =25A, R _{GEN} =3Ω, V _{GS} =4.5V	-	15	-	ns
t _r	Turn-on Rise Time		-	37	-	ns
t _{d(off)}	Turn-off Delay Time		-	52	-	ns
t _f	Turn-off Fall Time		-	21	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	60	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	240	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	IF=25A,dl/dt=100A/μs	-	25	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	21	-	nC

- Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
 2. EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=10V$, $V_G=4.5V$, $L=0.5mH$, $R_G=25\Omega$, $I_{AS}=13.8A$
 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

RATING AND CHARACTERISTIC CURVES (60N02)

Figure1: Output Characteristics

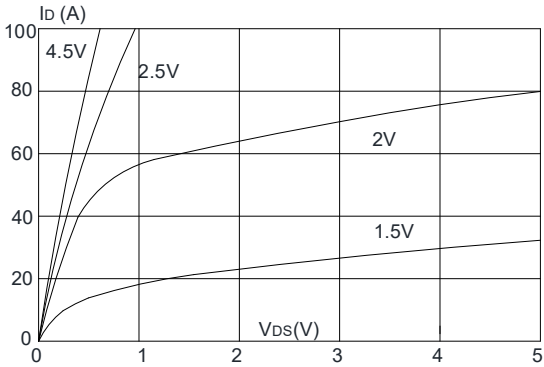


Figure 2: Typical Transfer Characteristics

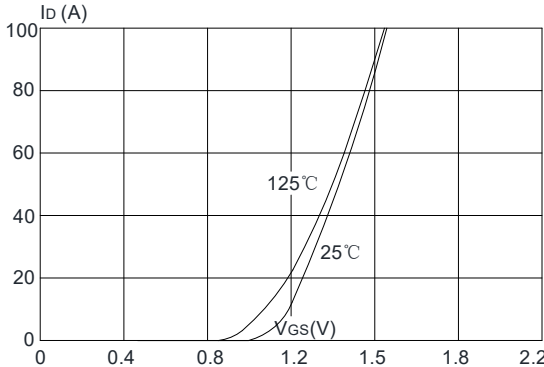


Figure 3: On-resistance vs. Drain Current

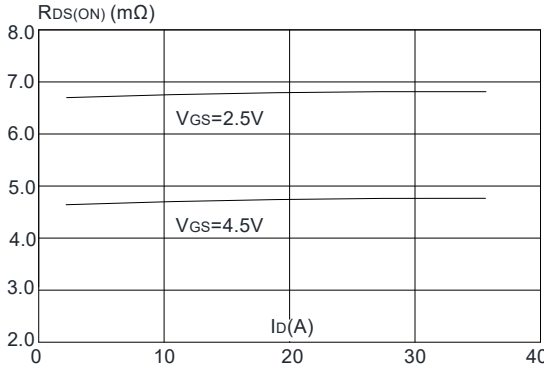


Figure 4: Body Diode Characteristics

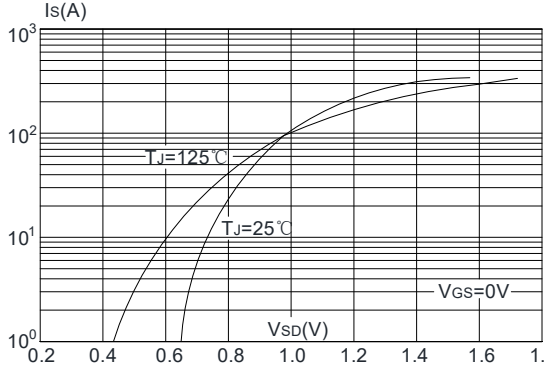


Figure 5: Gate Charge Characteristics

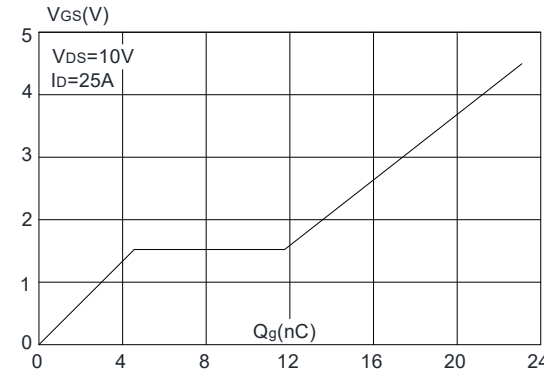
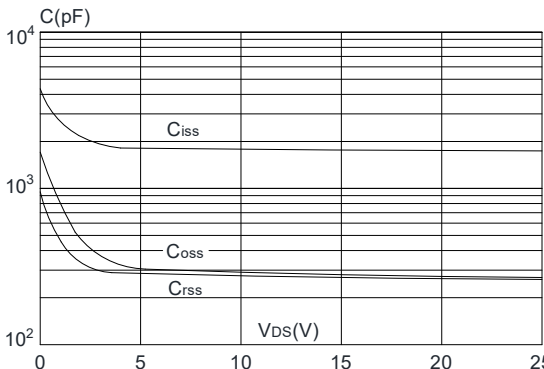


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES (60N02)

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

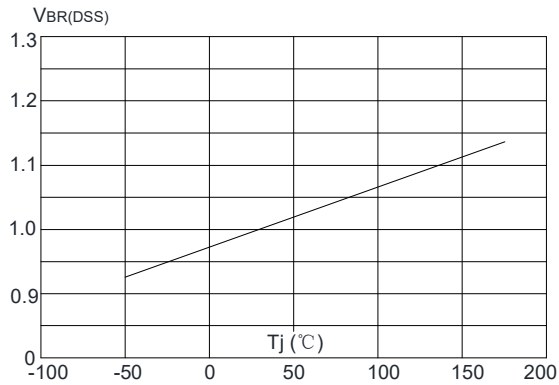


Figure 8: Normalized on Resistance vs. Junction Temperature

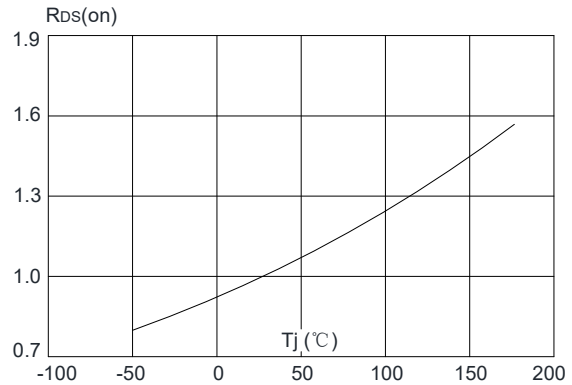


Figure 9: Maximum Safe Operating Area

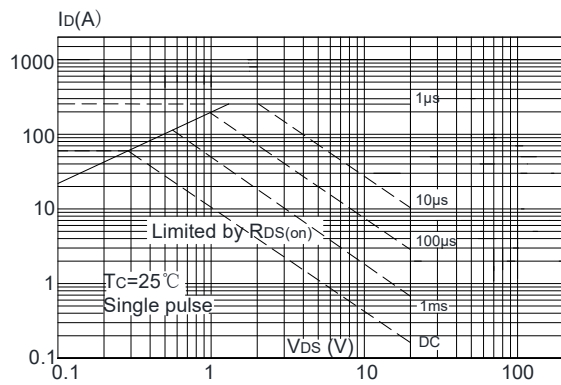


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

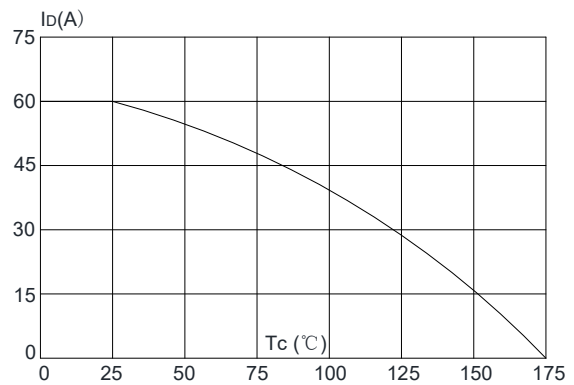


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

